NSN 5962-01-369-6584

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View Online at https://aerobasegroup.com/nsn/5962-01-369-6584

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Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
1.04 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Bipolar and high impedance and 3-state output and programmed and electrostatic sensitive and monolithic and schottky
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
14 input
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
190.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.3 volts power source and 7.0 volts power source
Capitance Rating Per Characteristic:
10.00 input picofarads and 13.00 output picofarads
Time Rating Per Chacteristic:
55.00 nanoseconds af output megawatts
Memory Device Type:
Prom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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